

## EAST Search History

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	134/33,94.1,95.2,137,149.ccls. and (((substrate wafer semiconductor workpiece) near5 (rins\$3 wash\$3 clean\$3)) and ((surface area region) near5 ("both" mixed) near5 (hydrophobic and hydrophilic))).clm.	US-PGPUB	OR	ON	2010/12/14 10:41
L2	1	134/33,94.1,95.2,137,149.ccls. and (((substrate wafer semiconductor workpiece) and (rins\$3 wash\$3 clean\$3)) and ((surface area region) and ("both" mixed) and (hydrophobic and hydrophilic))).clm.	US-PGPUB	OR	ON	2010/12/14 10:42
L3	1	134/33,94.1,95.2,137,149.ccls. and ((substrate wafer semiconductor workpiece) and (rins\$3 wash\$3 clean\$3) and (surface area region) and hydrophobic and hydrophilic and water).clm.	US-PGPUB	OR	ON	2010/12/14 10:45
S1	1	"20070131256".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 14:52
S2	2	("20080173333"   "5997653").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 14:53
S3	1	S1 and (hydrophobic hydrophilic)	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 15:24
S4	2	S2 and (hydrophobic hydrophilic)	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 15:24
S5	1	"20030084925".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 15:26
S6	0	S2 and S5	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 15:26
S7	3	S2 S5	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 15:26
S8	3	S7 and (hydrophobic hydrophilic)	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 15:26
S9	1006	((hydrophobic and hydrophilic) same (substrate wafer semiconductor workpiece)) and ((rins\$3 wash\$3 clean\$3) same (water near3 (pure\$2 purif\$3 purification demin demineraliz\$5)))	US-PGPUB; USPAT	OR	ON	2010/05/07 15:34
S10	728	S9 and water same film	US-PGPUB; USPAT	OR	ON	2010/05/07 15:36
S11	564	S10 and water same (reduc\$3 less lessen\$3 small\$2)	US-PGPUB; USPAT	OR	ON	2010/05/07 15:37

S12	141	S11 and water same (reduc\$3 less lessen\$3 small\$2) same (mov\$3 rotat \$3)	US-PGPUB; USPAT	OR	ON	2010/05/07 15:38
S13	114	S12 and water same (suppl\$4 feed\$3 using use\$1) same (reduc\$3 less lessen\$3 small\$2) same (mov\$3 rotat \$3)	US-PGPUB; USPAT	OR	ON	2010/05/07 15:39
S14	29	S13 and water same (suppl\$4 feed\$3 using use\$1) same (reduc\$3 less lessen\$3 small\$2) same (mov\$3 rotat \$3) same film	US-PGPUB; USPAT	OR	ON	2010/05/07 15:39
S15	1	"20030084925".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 17:39
S16	1	S15 and (hydrophobic hydrophilic)	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 17:39
S17	1006	((hydrophobic and hydrophilic) same (substrate wafer semiconductor workpiece)) and ((rins\$3 wash\$3 clean\$3) same (water near3 (pure\$2 purif\$3 purification demin demineraliz\$5)))	US-PGPUB; USPAT	OR	ON	2010/05/07 17:41
S18	182	S17 and (surface area) same ("both") same (hydrophobic and hydrophilic)	US-PGPUB; USPAT	OR	ON	2010/05/07 17:41
S19	21	S18 and (surface area) near5 ("both") near5 (hydrophobic and hydrophilic)	US-PGPUB; USPAT	OR	ON	2010/05/07 17:42
S20	6	("5882433"   "6221168"   "6398975"   "6406551"   "6491764").PN. OR ("7011715").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 17:48
S21	4	S20 and (hydrophobic and hydrophilic)	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 17:48
S22	189	S17 and (surface area region) same ("both") same (hydrophobic and hydrophilic)	US-PGPUB; USPAT	OR	ON	2010/05/07 17:50
S23	397	((substrate wafer semiconductor workpiece) near5 (rins\$3 wash\$3 clean\$3)) and ((surface area region) near5 ("both" mixed) near5 (hydrophobic and hydrophilic))	US-PGPUB; USPAT	OR	ON	2010/05/07 17:52
S24	90	S23 and ((substrate wafer semiconductor workpiece) near5 (rins \$3 wash\$3 clean\$3) near5 water)	US-PGPUB; USPAT	OR	ON	2010/05/07 17:53
S25	1	"6058945".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2010/05/07 22:51
S26	2	"2003197590".pn.	FPRS; EPO; JPO; DERWENT	OR	ON	2010/05/08 01:15
S27	64	(hydrophobic and hydrophilic) and (substrate wafer semiconductor workpiece) and (rins\$3 wash\$3 clean \$3) and (water near3 (pure\$2 purif \$3 purification demin demineraliz \$5))	FPRS; EPO; JPO; DERWENT	OR	ON	2010/05/08 01:22

S28	22	S27 and (surface area region) and ("both" mixed)	FPRS; EPO; JPO; DERWENT	OR	ON	2010/05/08 01:24
S29	61	S27 and (surface area region)	FPRS; EPO; JPO; DERWENT	OR	ON	2010/05/08 01:24
S30	1	"20070131256".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 16:37
S31	4	("20030075204"   "20080173333"   "5997653"   "6058945").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 16:38
S32	1	S30 and (hydrophobic hydrophilic)	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 17:03
S33	1	S30 and thin\$4	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 17:13
S34	1	S30 and stop\$4	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 17:16
S35	1	S30 and transition\$3	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 17:20
S36	1	S30 and rotat\$4 same (transition\$3 rins\$3)	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 17:21
S37	1	S30 and rotat\$4 same (transition\$3 spin\$4)	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 17:23
S38	414	((substrate wafer semiconductor workpiece) near5 (rins\$3 wash\$3 clean\$3)) and ((surface area region) near5 ("both" mixed) near5 (hydrophobic and hydrophilic))	US-PGPUB; USPAT	OR	ON	2010/12/13 17:28
S39	99	S38 and ((substrate wafer semiconductor workpiece) near5 (rins\$3 wash\$3 clean\$3) near5 water)	US-PGPUB; USPAT	OR	ON	2010/12/13 17:29
S40	1	((substrate wafer semiconductor workpiece) near5 (rinse rinsing rinsed wash washing washed clean cleaning cleaned)) and ((surface area region) near5 ("both" mixed) near5 (hydrophobic and hydrophilic))	USOCR	OR	ON	2010/12/13 17:29
S41	65	(hydrophobic and hydrophilic) and (substrate wafer semiconductor workpiece) and (rins\$3 wash\$3 clean\$3) and (water near3 (pure\$2 purif\$3 purification demin demineraliz\$5))	FPRS; EPO; JPO; DERWENT	OR	ON	2010/12/13 17:30
S42	23	S41 and (surface area region) and ("both" mixed)	FPRS; EPO; JPO; DERWENT	OR	ON	2010/12/13 17:30
S43	123	S39 S40 S42	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2010/12/13 17:31

S44	93	S43 and (((film layer\$3 coat\$3) near5 (thin\$3 less\$2 small\$3 decreas\$3 reduc\$3)) or ((feed\$3 flow\$3 flowrate suppl\$4) near5 (less\$2 small\$3 decreas\$3 reduc\$3)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2010/12/13 17:34
S45	1	"20020130106".PN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 18:18
S46	5	S31 S45	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 18:18
S47	0	("2008/0173333").URPN.	USPAT	OR	ON	2010/12/13 18:18
S48	11	("2003/0075204").URPN.	USPAT	OR	ON	2010/12/13 18:18
S49	2	("2002/0130106").URPN.	USPAT	OR	ON	2010/12/13 18:18
S50	18	("3893869"   "4927781"   "5331180"   "5372962"   "5427977"   "5510633"   "5626159").PN. OR ("6058945").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 18:19
S51	107	("4027686"   "4871417"   "5248380"   "5351360"   "5372652"   "5456758"   "5558110").PN. OR ("5997653").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 18:19
S52	132	S47 S48 S49 S50 S51	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 18:19
S53	63	S52 and ((substrate wafer semiconductor workpiece) near5 (rins\$3 wash\$3 clean\$3) near5 water)	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 18:19
S54	1	S52 and ((substrate wafer semiconductor workpiece) near5 (rins\$3 wash\$3 clean\$3)) and ((surface area region) near5 ("both" mixed) near5 (hydrophobic and hydrophilic))	US-PGPUB; USPAT; USOCR	OR	ON	2010/12/13 18:20

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